

Homework #4 (gate sizing)

Problem #1. Consider the delay model that we've used for our sizing unit, where

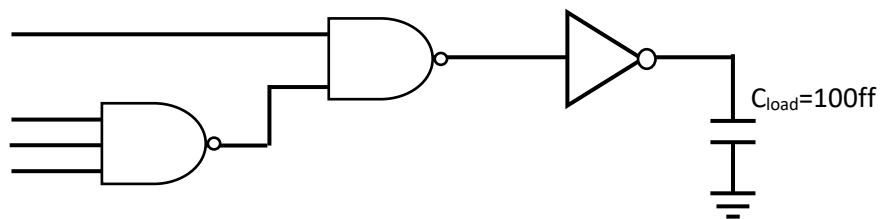
- Device resistance $R = k_{\text{dev}R} L/W$ (where $k_{\text{dev}R}$ has units of ohms)
- Self-loading capacitance of a device $C_{\text{self}} = k_{\text{self}} * W$ (where k_{self} has units of ff/DU)
- Delay $D = R * (C_{\text{self}} + C_{\text{load}})$
- $C_{\text{in}} = k_{\text{gate}} * L * W$ (where k_{gate} has units of ff/DU²). I.e., this is the input capacitance of a gate as a function of the gate's device sizes (the sum of the N-device and P-device gate areas on any of the gate's inputs).

Note that for simplicity, we've ignored wire resistance. Consider a simple inverter driving a fixed loading capacitor. Prove that, for a given delay D :

1. The width W is directly proportional to C_{load} : i.e., $W = k * C_{\text{load}}$ for some constant k that depends on D .
2. The gain of the gate ($C_{\text{load}}/C_{\text{in}}$) is constant; it does not depend on the load.
3. The self-loading fraction $C_{\text{self}}/(C_{\text{self}}+C_{\text{load}})$ is constant; it does not depend on the load.

Problem #2.

Consider the network shown below. Size it assuming that all transistors have $L=2\text{DU}$ and that all inverters have a gain of 3. At this gain, inverters have a delay of roughly 45ps, and $W_{n,\text{eff}} = (2.8\text{DU}/\text{ff}) * C_{\text{load}}$. Assume that device input capacitance $C_{\text{in}} = .02 \text{ ff/DU}^2$. Size the NAND gates to have roughly (i.e., other than self loading) the same 45ps delay as the inverters, as we discussed in class (this will result in them having a gain less than 3).



Please turn in your assignment via the Provide cgi interface. You can use any reasonable format (including writing your answers by hand and taking a picture of the page with your phone).